

PHP225

Dual P-channel intermediate level FET Rev. 04 — 17 March 2011

Product data sheet

Product profile 1.

1.1 General description

Dual intermediate level P-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using vertical D-MOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- Motor and actuator drivers
- Power management

Synchronized rectification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}$		-	-	-30	V
I _D	drain current	T _{sp} ≤ 80 °C		-	-	-2.3	Α
P _{tot}	total power dissipation	T _{sp} = 80 °C	[1]	-	-	2	W
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -10 \text{ V}; I_D = -1 \text{ A};$ $T_j = 25 \text{ °C}$		-	0.22	0.25	Ω
Dynamic ch	naracteristics						
Q_{GD}	gate-drain charge	V_{GS} = -10 V; I_D = -2.3 A; V_{DS} = -15 V; T_j = 25 °C		-	3	-	nC

^[1] Maximum permissible dissipation per MOS transistor. Both devices may be loaded up to 2 W at the same



Dual P-channel intermediate level FET

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		D. D. D. D.
2	G1	gate1	8 <u> </u>	D1 D1 D2 D2
3	S2	source2		
4	G2	gate2		
5	D2	drain2	1	S1 G1 S2 G2
6	D2	drain2	SOT96-1 (SO8)	sym115
7	D1	drain1		
8	D1	drain1		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHP225	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

Dual P-channel intermediate level FET

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}$		-	-30	V
gate-source voltage			-	-	V
gate-source voltage	open drain		-20	20	V
drain current	T _{sp} ≤ 80 °C		-	-2.3	Α
peak drain current	T _{sp} = 25 °C; pulsed	<u>[1]</u>	-	-10	Α
total power dissipation	T _{amb} = 25 °C	[2]	-	1	W
	T _{sp} = 80 °C	[3]	-	2	W
	T _{amb} = 25 °C	<u>[4]</u>	-	1.3	W
		[5]	-	2	W
storage temperature			-65	150	°C
junction temperature			-	150	°C
n diode					
source current	T _{sp} ≤ 80 °C		-	-1.25	Α
peak source current	T _{sp} = 25 °C; pulsed	<u>[1]</u>	-	-5	Α
	drain-source voltage gate-source voltage gate-source voltage drain current peak drain current total power dissipation storage temperature junction temperature n diode source current	$\begin{array}{ll} \text{drain-source voltage} & T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 150 \ ^{\circ}\text{C} \\ \\ \text{gate-source voltage} & \text{open drain} \\ \\ \text{drain current} & T_{sp} \leq 80 \ ^{\circ}\text{C} \\ \\ \text{peak drain current} & T_{sp} = 25 \ ^{\circ}\text{C}; \ \text{pulsed} \\ \\ \text{total power dissipation} & T_{amb} = 25 \ ^{\circ}\text{C} \\ \\ \hline T_{amb} = 25 \ ^{\circ}\text{C} \\ \\ \hline T_{amb} = 25 \ ^{\circ}\text{C} \\ \\ \hline \end{array}$	$\begin{array}{lll} & \text{drain-source voltage} & T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 150 \ ^{\circ}\text{C} \\ & \text{gate-source voltage} \\ & \text{gate-source voltage} & \text{open drain} \\ & \text{drain current} & T_{sp} \leq 80 \ ^{\circ}\text{C} \\ & \text{peak drain current} & T_{sp} = 25 \ ^{\circ}\text{C}; \ \text{pulsed} & \boxed{11} \\ & \text{total power dissipation} & \overline{T_{amb}} = 25 \ ^{\circ}\text{C} & \boxed{2} \\ & \overline{T_{sp}} = 80 \ ^{\circ}\text{C} & \boxed{3} \\ & \overline{T_{amb}} = 25 \ ^{\circ}\text{C} & \boxed{4} \\ \hline & \boxed{5} \\ & \text{storage temperature} \\ & \text{junction temperature} \\ & \text{n diode} \\ & \text{source current} & T_{sp} \leq 80 \ ^{\circ}\text{C} \\ & \end{array}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

^[1] Pulse width and duty cycle limited by maximum junction temperature.

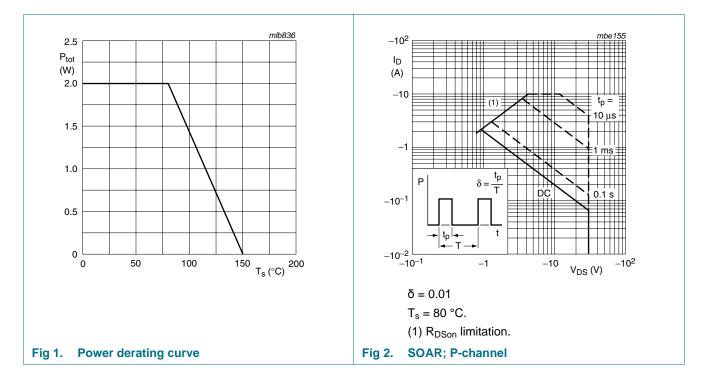
^[2] Maximum permissible dissipation per MOS transistor. Device mounted on printed-circuit board with a thermal resistance from ambient to tie-point of 90 K/W.

^[3] Maximum permissible dissipation per MOS transistor. Both devices may be loaded up to 2 W at the same time.

^[4] Maximum permissible dissipation if only one MOS transistor dissipates. Device mounted on printed-circuit board with a thermal resistance from ambient to tie-point of 90 K/W.

^[5] Maximum permissible dissipation per MOS transistor. Device mounted on printed-circuit board with a thermal resistance from ambient to tie-point of 27.5 K/W.

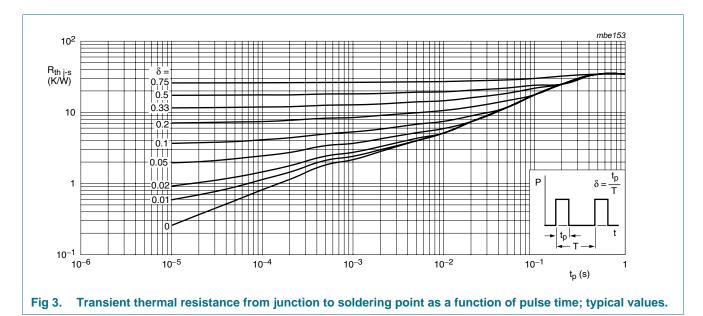
Dual P-channel intermediate level FET



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	see Figure 3	-	-	35	K/W



Dual P-channel intermediate level FET

6. Characteristics

Table 6. Characteristics

Table 0.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = -1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1	-	-2.8	V
I _{DSS}	drain leakage current	$V_{DS} = -24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon}	drain-source on-state	$V_{GS} = -10 \text{ V}; I_D = -1 \text{ A}; T_j = 25 \text{ °C}$	-	0.22	0.25	Ω
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -0.5 \text{ A}; T_j = 25 \text{ °C}$	-	0.33	0.4	Ω
I _{DSon} on-state drain current	V _{DS} = -1 V; V _{GS} = -10 V	-2.3	-	-	Α	
		V _{DS} = -5 V; V _{GS} = -4.5 V	-1	-	-	Α
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = -2.3 \text{ A}; V_{DS} = -15 \text{ V}; V_{GS} = -10 \text{ V};$	-	10	25	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1	-	nC
Q_{GD}	gate-drain charge		-	3	-	nC
C _{iss}	input capacitance	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	250	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	140	-	pF
C _{rss}	reverse transfer capacitance		-	50	-	pF
g _{fs}	transfer conductance	V_{DS} = -20 V; I_{D} = -1 A; T_{j} = 25 °C	1	2	-	S
t _{off}	turn-off time	V_{DS} = -20 V; V_{GS} = -10 V; $R_{G(ext)}$ = 4.7 Ω ;	-	50	140	ns
t _{on}	turn-on time	$R_L = 20 \Omega; T_j = 25 \text{ °C}; I_D = -1 \text{ A}$	-	20	80	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = -1.25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1.6	V
t _{rr}	reverse recovery time	$I_S = -1.25 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$; $V_{DS} = 25 \text{ V}$; $T_j = 25 \text{ °C}$	-	150	200	ns

Dual P-channel intermediate level FET

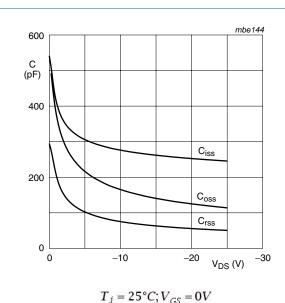
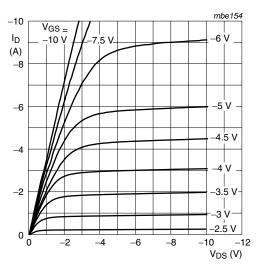


Fig 4. Capacitance as a function of drain-source voltage; P-channel; typical values



$$T_j = 25^{\circ}C$$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; P-channel; typical values

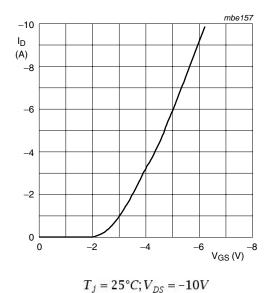
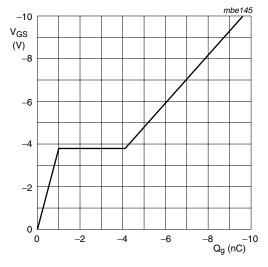


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; P-channel; typical values



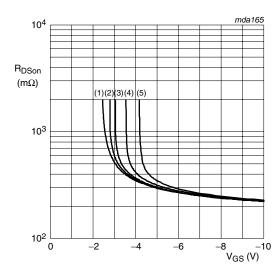
$$I_D = -2.3A; V_{DS} = -15V$$

Fig 7. Gate-source voltage as a function of gate charge; P-channel; typical values

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 $-V_{DS} \ge -I_D \times R_{DSon}$; $T_j = 25 \, ^{\circ}C$.

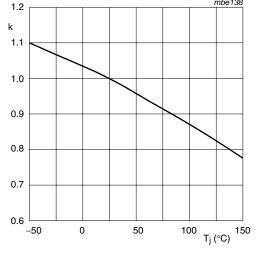
(1)
$$I_D = -0.1 A$$
.

(2)
$$I_D = -0.5 A$$
.

(3)
$$I_D = -1 A$$
.

(4)
$$I_D = -2.3 A$$
.

(5)
$$I_D = -4.5 A$$
.

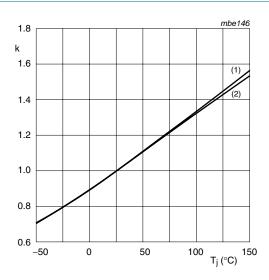


$$k = \frac{V_{GSth} \text{ at } T_j}{V_{GSth} \text{ at } 25^{\circ}C}$$

Typical V_{GSth} at $I_D = 1$ mA; $V_{DS} = V_{GS} = V_{GSth}$.







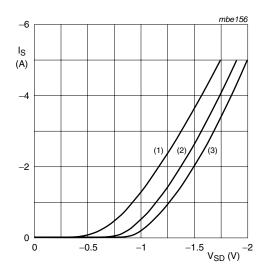
$$k = \frac{R_{DSon} \operatorname{at} T_{j}}{R_{DSon} \operatorname{at} 25^{\circ} C}$$

Typical R_{DSon} at:

(1)
$$I_D = -1 A$$
; $V_{GS} = -10 V$.

(2)
$$I_D = -0.5 \text{ A}$$
; $V_{GS} = -4.5 \text{ V}$.

Fig 10. Temperature coefficient of drain-source on-state resistance; P-channel



$$V_{GD} = 0V(1)T_j = 150^{\circ}C(2)T_j = 25^{\circ}C(3)T_j = -55^{\circ}C$$

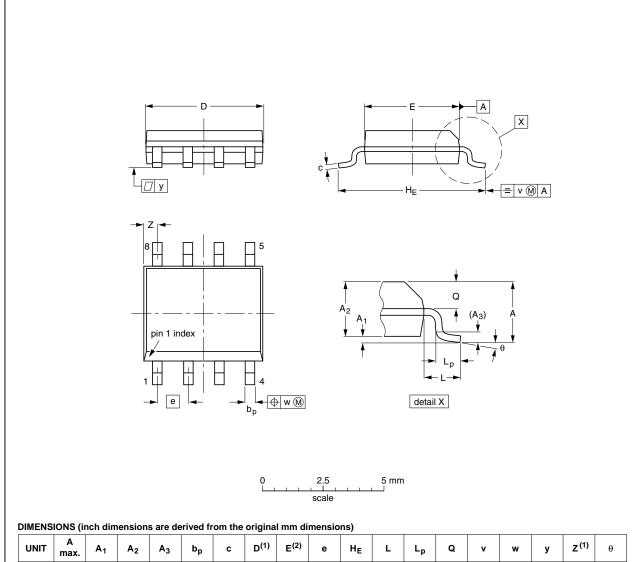
Fig 11. Source current as a function of source-drain voltage

Dual P-channel intermediate level FET

7. Package outline

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	σ	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

	REFER	EUROPEAN	ISSUE DATE		
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
076E03	MS-012				99-12-27 03-02-18
		IEC JEDEC		IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

Fig 12. Package outline SOT96-1 (SO8)

PHP225

Dual P-channel intermediate level FET

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP225 v.4	20110317	Product data sheet	-	PHP225 v.3
Modifications:	 Various changes to 	content.		
PHP225 v.3	20110104	Product data sheet	-	PHP225 v.2

Dual P-channel intermediate level FET

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Dual P-channel intermediate level FET

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Dual P-channel intermediate level FET

11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data
2	Pinning information
3	Ordering information
4	Limiting values
5	Thermal characteristics
6	Characteristics
7	Package outline
8	Revision history
9	Legal information1
9.1	Data sheet status
9.2	Definitions10
9.3	Disclaimers
9.4	Trademarks1
10	Contact information

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